



N-Channel Depletion-Mode DMOS FET

Features

- ▶ Free from secondary breakdown
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ High input impedance and low C_{iss}
- ▶ ESD gate protection

Applications

- ▶ Solid state relays
- ▶ Normally-on switches
- ▶ Converters
- ▶ Power supply circuits
- ▶ Constant current sources
- ▶ Input protection circuits

General Description

The LND250 is a high voltage N-channel depletion mode (normally-on) transistor utilizing Supertex's lateral DMOS technology. The gate is ESD protected.

The LND250 is ideal for high voltage applications in the areas of normally-on switches, precision constant current sources, voltage ramp generation and amplification.

Ordering Information

| Part Number | Package Options | Packing |
|-------------|-------------------|-----------|
| LND250K1-G* | TO-236AB (SOT-23) | 3000/Reel |

*G denotes a lead (Pb)-free / RoHS compliant package

* Part is not recommended for new designs. Please refer to LND150K1-G.

Absolute Maximum Ratings

| Parameter | Value |
|-----------------------------------|-----------------|
| Drain-to-source | BV_{DSX} |
| Drain-to-gate | BV_{DGX} |
| Gate-to-source | $\pm 20V$ |
| Operating and storage temperature | -55°C to +150°C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Product Summary

| BV_{DSX}/BV_{DGX} (V) | $R_{DS(ON)}$ (max) | I_{DSS} (min) |
|----------------------------|-----------------------|--------------------|
| 500 | 1.0k Ω | 1.0mA |

Pin Configuration



TO-236AB (SOT-23)

Product Marking

NDEW

W = Code for Week Sealed
____ = "Green" Packaging

TO-236AB (SOT-23)

Packages may or may not include the following marks: Si or 

Thermal Characteristics

| Package | I_D (continuous) [†] (mA) | I_D (pulsed) (mA) | Power Dissipation @ $T_A = 25^\circ\text{C}$ (W) | θ_{JA} (°C/W) | I_{DR} (mA) | I_{DRM} (mA) |
|-------------------|--|---------------------------|--|-------------------------|------------------|-------------------|
| TO-236AB (SOT-23) | 13 | 30 | 0.36 | 203 | 13 | 30 |

Notes:

[†] I_D (continuous) is limited by max rated T_J

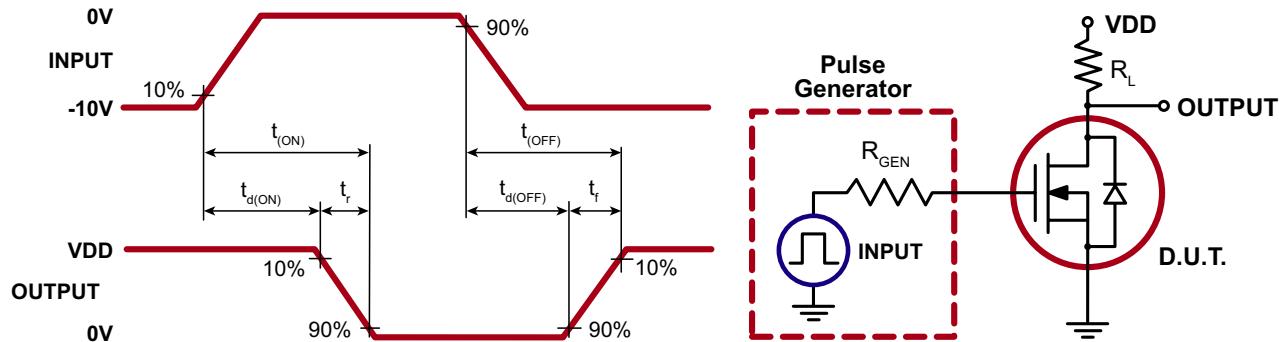
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Sym | Parameter | Min | Typ | Max | Units | Conditions |
|-----------------------------|---|------|------|------|-------|--|
| BV_{DSX} | Drain-to-source breakdown voltage | 500 | - | - | V | $V_{GS} = -10\text{V}$, $I_D = 1.0\text{mA}$ |
| $V_{GS(\text{OFF})}$ | Gate-to-source off voltage | -1.0 | - | -3.0 | V | $V_{GS} = 25\text{V}$, $I_D = 100\text{nA}$ |
| $\Delta V_{GS(\text{OFF})}$ | Change in $V_{GS(\text{OFF})}$ with temperature | - | - | 5.0 | mV/°C | $V_{GS} = 25\text{V}$, $I_D = 100\text{nA}$ |
| I_{GSS} | Gate body leakage current | - | - | 100 | nA | $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$ |
| $I_{D(\text{OFF})}$ | Drain-to-source leakage current | - | - | 100 | nA | $V_{GS} = -10\text{V}$, $V_{DS} = 450\text{V}$ |
| | | - | - | 100 | μA | $V_{DS} = 0.8\text{V}$ Max Rating, $V_{GS} = -10\text{V}$, $T_A = 125^\circ\text{C}$ |
| I_{DSS} | Saturated drain-to-source current | 1.0 | - | 3.0 | mA | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$ |
| $R_{DS(\text{ON})}$ | Static drain-to-source on-state resistance | - | 850 | 1000 | Ω | $V_{GS} = 0\text{V}$, $I_D = 0.5\text{mA}$ |
| $\Delta R_{DS(\text{ON})}$ | Change in $R_{DS(\text{ON})}$ with temperature | - | - | 1.2 | %/°C | $V_{GS} = 0\text{V}$, $I_D = 0.5\text{mA}$ |
| G_{FS} | Forward transductance | 1.0 | 2.0 | - | mmho | $V_{DS} = 0\text{V}$, $I_D = 1.0\text{mA}$ |
| C_{ISS} | Input capacitance | - | 7.5 | 10 | pF | $V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$, $f = 1.0\text{MHz}$ |
| C_{OSS} | Common source output capacitance | - | 2.0 | 3.5 | | |
| C_{RSS} | Reverse transfer capacitance | - | 0.5 | 1.0 | | |
| $t_{d(\text{ON})}$ | Turn-on delay time | - | 0.09 | - | | |
| t_r | Rise time | - | 0.45 | - | μs | $V_{DD} = 25\text{V}$, $I_D = 1.0\text{mA}$, $R_{GEN} = 25\Omega$ |
| $t_{d(\text{OFF})}$ | Turn-off delay time | - | 0.1 | - | | |
| t_f | Fall time | - | 1.3 | - | | |
| V_{SD} | Diode forward voltage drop | - | - | 0.9 | V | $V_{GS} = -10\text{V}$, $I_{SD} = 1.0\text{mA}$ |
| t_{rr} | Reverse recovery time | - | 200 | - | ns | $V_{GS} = -10\text{V}$, $I_{SD} = 1.0\text{mA}$ |

Notes:

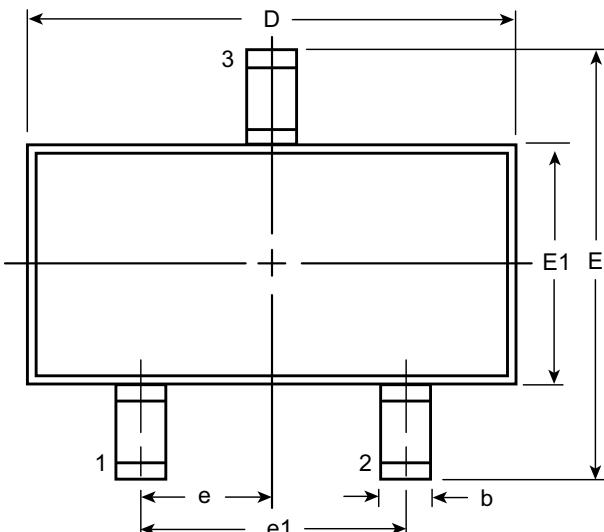
- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

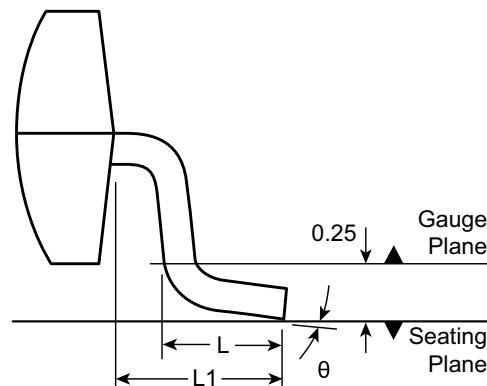


3-Lead TO-236AB (SOT-23) Package Outline (K1)

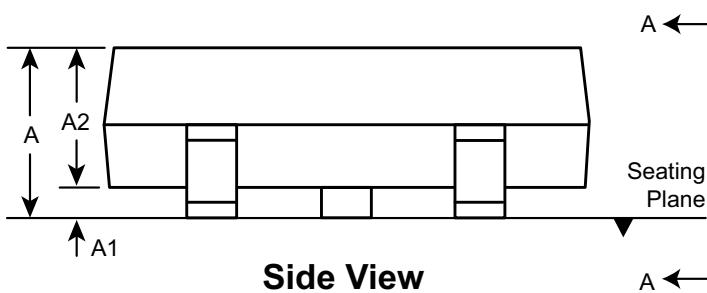
2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



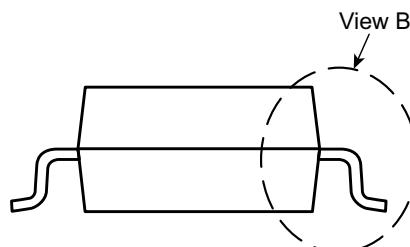
Top View



View B



Side View



View A - A

| Symbol | A | A1 | A2 | b | D | E | E1 | e | e1 | L | L1 | θ |
|----------------|-----|------|------|------|------|------|------|------|----------|-------------------|----------|----------------|
| Dimension (mm) | MIN | 0.89 | 0.01 | 0.88 | 0.30 | 2.80 | 2.10 | 1.20 | 0.95 BSC | 0.20 [†] | 0.54 REF | 0 ^o |
| | NOM | - | - | 0.95 | - | 2.90 | - | 1.30 | | | | |
| | MAX | 1.12 | 0.10 | 1.02 | 0.50 | 3.04 | 2.64 | 1.40 | | | | |

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

[†] This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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